## **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

- 1. (Currently amended) A method of depositing  $Hg_{1-x}Cd_xTe$ , where 0 < x < 1, onto a substrate, in a MOVPE technique, where  $0 \le x \le 1$ ; comprising the step of reacting together isopropylallyltelluridea volatile organotellurium compound, and one or both of (i) a volatile organocadmium compound and (ii) mercury vapour vapor, wherein  $Hg_{1-x}Cd_xTe$  is grown by an interdiffused multilayer process involving the alternate growth of cadmium telluride and mercury telluride layers, which are then interdiffused to produce  $Hg_{1-x}Cd_xTe$ ; characterised in that the organotellurium compound is isopropylallyltelluride and in that and wherein the substrate is maintained at a temperature in the range  $150^{\circ}C$  to  $350^{\circ}C$ .
- 2. (Original) A method of depositing Hg<sub>1-x</sub>Cd<sub>x</sub>Te according to Claim 1 wherein the organocadmium compound is an alkyl cadmium compound.
- 3. (Original) A method of depositing Hg<sub>1-x</sub>Cd<sub>x</sub>Te according to Claim 2 wherein the alkyl cadmium compound is dimethyl cadmium.
- 4. (Cancelled)
- 5. (Cancelled)
- 6. (Cancelled)
- 7. (Cancelled)

HAILS, J. et al. Appl. No. 10/088,026 September 7, 2005

8. (Original) A method of depositing Hg<sub>1-x</sub>Cd<sub>x</sub>Te according to Claim 1 wherein the substrate comprises glass, or glass coated with indium tin oxide, or CdTe, or CdZnTe, or GaAs, or

GaAs/Si, or CdTe/GaAs, or Si.

9. (Original) A method of depositing Hg<sub>1-x</sub>Cd<sub>x</sub>Te according to Claim 1 wherein the temperature

of the substrate is maintained at a temperature in the range 150°C to 300°C.

10. (Original) A method of depositing Hg<sub>1-x</sub>Cd<sub>x</sub>Te according to Claim 9 wherein the temperature

of the substrate is maintained at a temperature in the range 250°C to 300°C.

11. (Previously amended) A method of fabricating an electronic device comprising the steps of

(a) depositing Hg<sub>1-x</sub>Cd<sub>x</sub>Te onto a substrate by a method according to Claim 1; and (b) connecting

at least two electrodes to the  $Hg_{1-x}Cd_xTe$ .

12. (Original) A method of fabricating an electronic device according to Claim 11 wherein the

method further comprises the step of doping the Hg<sub>1-x</sub>Cd<sub>x</sub>Te.

13. (Currently amended) A method of fabricating an electronic device according to Claim 11

wherein the method comprises the further step of doping the Hg<sub>1-x</sub>Cd<sub>x</sub>Te material in such a

manner that a p-n junction is formed.

14. (Previously amended) A method of fabricating a device according to Claim 11 wherein the

method further comprises the step of growing a passivating layer of CdTe on the Hg<sub>1-x</sub> Cd<sub>x</sub>Te.

15. (Cancelled)

16. (Cancelled)

17. (Cancelled)

- 3 -

990633

HAILS, J. et al. Appl. No. 10/088,026 September 7, 2005

18. (Cancelled)

19. (New) A method of depositing Hg<sub>1-x</sub>Cd<sub>x</sub>Te according to Claim 1, wherein the cadmium telluride layer is deposited in the presence of mercury vapor.